

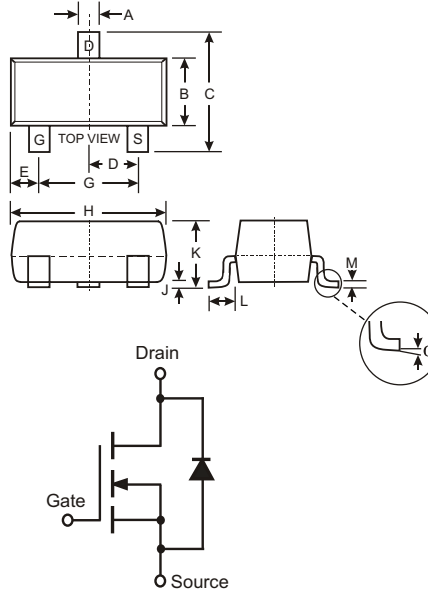
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Mechanical Data

- Case: SOT-23, Molded Plastic
- Case Material - UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking (See Page 2): K70
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	BS870	Units
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 1)	I_D	250	mA
Total Power Dissipation (Note 1)	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	K/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Note: 1. Device mounted on FR-5 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

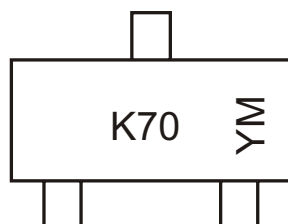
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	80	—	V	V _{GS} = 0V, I _D = 100μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 25V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±15V, V _{DS} = 0V
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(th)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.5	5.0	Ω	V _{GS} = 10V, I _D = 0.2A
On-State Drain Current	I _{D(ON)}	—	1.0	0.5	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	22	50	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	2.0	20	ns	V _{ES} = 10V, R _L = 150Ω, V _{DS} = 10V, R _D = 100Ω
Turn-Off Delay Time	t _{D(OFF)}	—	5.0	20	ns	

Ordering Information (Note 3)

Device	Packaging	Shipping
BS870-7	SOT-23	3000/Tape & Reel

- Notes: 2. Short duration test pulse used to minimize self-heating effect.
3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

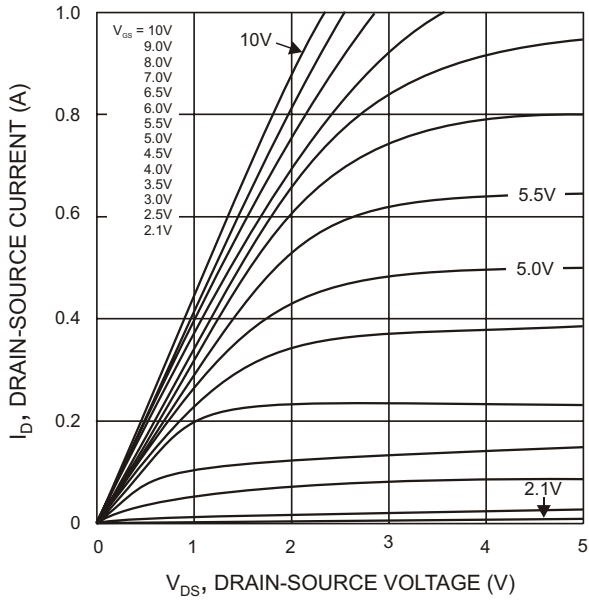
Marking Information



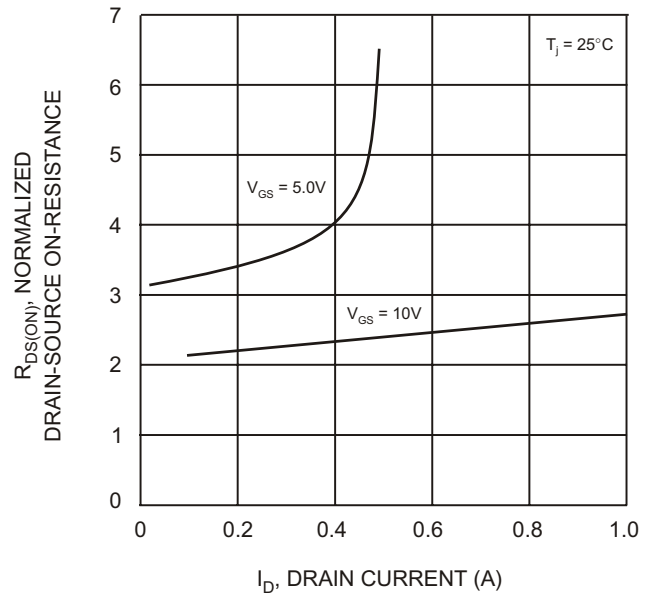
K70 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

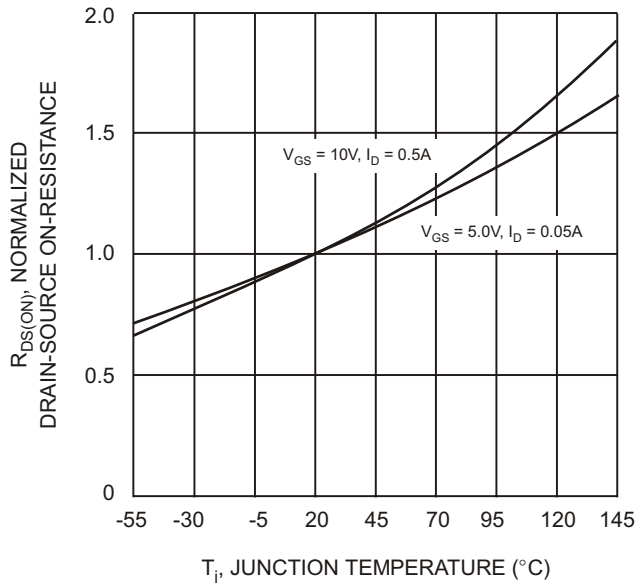
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



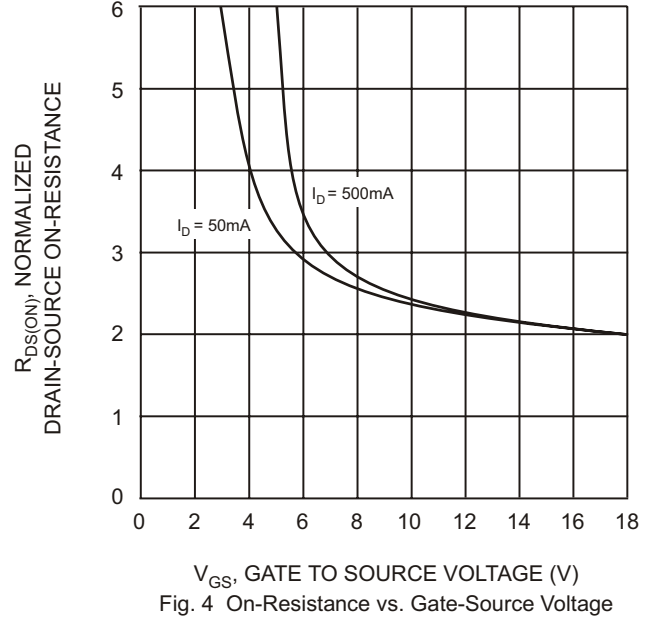
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Fig. 1 On-Region Characteristics



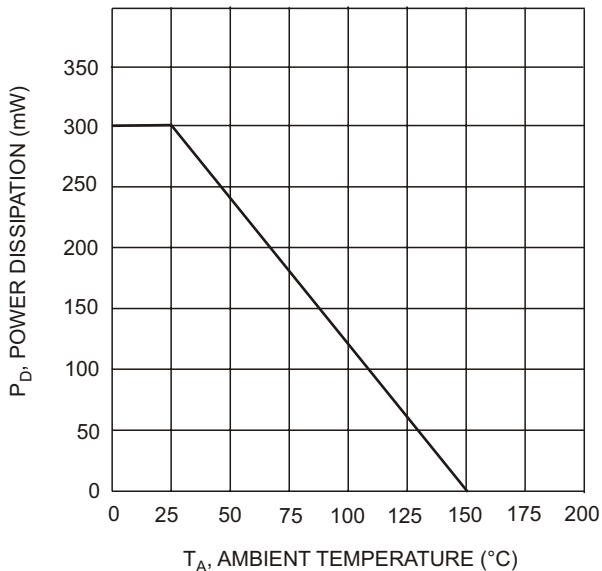
I_D , DRAIN CURRENT (A)
Fig. 2 On-Resistance vs Drain Current



T_J , JUNCTION TEMPERATURE (°C)
Fig. 3 On-Resistance vs Junction Temperature



V_{GS} , GATE TO SOURCE VOLTAGE (V)
Fig. 4 On-Resistance vs. Gate-Source Voltage



T_A , AMBIENT TEMPERATURE (°C)
Fig. 5, Max Power Dissipation vs Ambient Temperature



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